

PREAMPLIFIER ON PREAMPLIFIER ON POWER NO. 205 NO. 205

Amplifiers for infrared detector

C4159 series

Low noise amplifiers for infrared detector (InSb, InAs, InAsSb, InGaAs)

These are high gain and low noise amplifiers for Hamamatsu various infrared detectors. By connecting a detectior and supplying the power, analog voltage output can be obtained and the signal can be easily observed with a voltmeter or the like. Amplifiers that match the characteristics of infrared detectors are available.

Features

- Voltage output for easy handling
- Conversion impedance: 3 ranges switchable (C4159 series)
- Compact: business card size

Accessories

- **■** Instruction manual
- → Power cable A4372-02

 (one end with 4-pin connector for connection to amplifier and the other end unterminated, 2 m)

Applications

- Spectrophotometers
- Radiation thermometers
- **→** Laser power monitor

Required power supply specifications

- · Output voltage: $\pm 15 \text{ V} \pm 0.5$
- · Current capacity: 1.5 times or more of amplifier's maximum current consumption
- · Ripple noise: 5 mVp-p or less
- · Analog power supply only

Recommended DC power supply: PW18-3AD (TEXIO)

E3630A (Keysight Technologies)

- Applicable detectors

Type	Type no.	Applicable detectors*1 *2 *3		
Amplifier for photovoltaic detectors		Dewar type InSb (P5968-060/-100), Non-cooled type InAsSb (P13243-011MA/-013CA/ -015CF/-016CF/-033CF/-033MF/-039CF/-039MF/-043CF/-043MF, P13894-011CN/ -011MA/-011NA), Tecooled type InAsSb (P13243-122MS/-222MS, P13894-211MA), Dewar type TypeII(P15409-901)		
		Dewar type InSb (P5968-200)		
	C4159-05	Dewar type InAs (P7163)		
	C4159-06	TE-cooled type InAs (P10090-11/-21)		
	C4159-07	Non-cooled type InAs (P10090-01), TE-cooled type InAsSb (P11120-201, P12691-201G)		
Amplifier for InGaAs PIN photodiodes	C4159-03	Non/TE-cooled type InGaAs (G12180/G12181/G12182/G12183 series)		

^{*1:} These amplifiers cannot operate multiple detectors.

→ Absolute maximum ratings (Ta=25 °C)

Parameter	Value	Unit
Supply voltage	18.0 max.	V
Operating temperature*4	0 to +40	°C
Storage temperature*4	-20 to +70	°C

^{*4:} No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and relaiablity.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

^{*2:} Consult us before purchasing if you want to use with a detector other than listed here.

^{*3:} Consult us before purchasing if you want to use with a multi-element detector.

Amplifiers for photovoltaic detectors (Typ.)

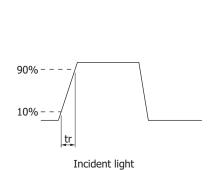
Parameter	C4159-01	C4159-04	C4159-05	C4159-06	C4159-07	Unit
Conversion impedance		2×10^7 , 2×10^6 , 2×10^5 (3 ranges switchable)		10^6 , 10^5 , 10^4 (3 ranges switchable)	10^6 , 10^5 , 10^4 (3 ranges switchable)	V/A
Frequency response (amplifier only, -3 dB)	DC to 100 kHz*5	DC to 45 kHz	DC to 15 kHz	DC to 100 kHz	DC to 100 kHz	-
Output impedance	50	50	50	50	50	Ω
Maximum output voltage (1 $k\Omega$ load)	+10	+10	+10	+10	+10	V
Output offset voltage	±5	±5	±10	±5	±5	mV
Equivalent input noise current*6 (f=1 kHz)	0.15 (10 ⁸ , 10 ⁷ range) 0.65 (10 ⁶ range)	0.55	0.15 (10 ⁸ , 10 ⁷ range) 0.65 (10 ⁶ range)	6	10	pA/Hz ^{1/2}
Reverse voltage	Limited to 0 V operation. Cannot be applied from external unit.				-	
External power supply*7	±15				V	
Current consumption	+30, -10 max. +30, -22 max.					mA

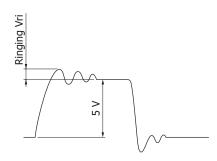
^{*5:} When connected to a detector, frequency response becomes 60 kHz or less (φ0.6 mm: 60 kHz or less, φ1 mm: 25 kHz or less). Ringing occurs in the output if the rise time tr (10 to 90%) of incident light is approximately 100 μs or less. The ringing becomes larger as the rise time becomes shorter. However, ringing does not occur for sine wave light. (For information on the ringing specifications, see the figure below.)

Note: Output noise voltage = Equivalent input noise current \times Conversion impedance

For information about accessories except for the amplifiers, refer to the datasheet "Accessories for infrared detector".

Ringing specifications





Output waveform when tr=40 μs and photosensitive area is $\varphi 0.6$ mm Ringing Vri ≤ 1.5 V Oscillating cycle ≤ 3 cycles

KIRDA0090EA

- Amplifier for InGaAs PIN photodiodes (Typ.)

Parameter	C4159-03	
Conversion impedance	10 ⁷ , 10 ⁶ , 10 ⁵ (3 ranges switchable)	
Frequency response (amp only, -3 dB)	DC to 15 kHz	-
Output impedance	50	Ω
Maximum output voltage (1 kΩ load)	+10	V
Output offset voltage	±5	mV
Equivalent input noise current (f=1 kHz)	2.5	pA/Hz ^{1/2}
Reverse voltage	Can be applied from external unit.	-
External power supply*8	±15	V
Current consumption	±15 max.	mA

^{*8:} Recommended DC power supply (analog power supply): ±15 V

Current capacity: More than 1.5 times the maximum current consumption

Ripple noise: 5 mVp-p or less

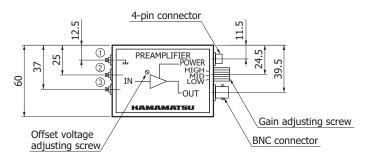


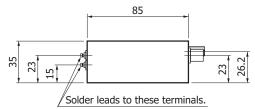
^{*6:} Input resistance: 1 M Ω (C4159-01/-04/-05), 500 Ω (C4159-06/-07)

^{*7:} Recommended DC power supply (analog power supply): ±15 V Current capacity: 1.5 times the maximum current consumption or more Ripple noise: 5 mVp-p or less

Dimensional outlines (unit: mm)

C4159-01/-03/-04/-05/-06/-07





Pin connections

- ① GND
- ② Cathode [input terminal (C4159-01/-04/-05/-06/-07)]
- ③ Anode [input terminal (C4159-03)]

Type no. Weight
C4159-01/-03/-04/-05 320 g
C4159-06/-07 330 g

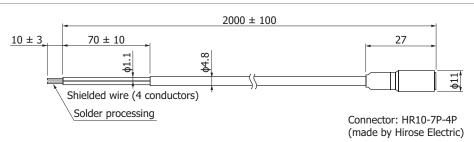
Tolerance unless otherwise noted: ±1

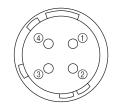
Note: Socket for lead attachment is not provided.

C4159-03: If no reverse bias is applied to a detector, connect the detector cathode to the amplifier GND.

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A4372-02





Pin no.	Pin connection	Lead color
1	-Vs	Blue
2	GND	Black/white/blue
3	GND	stranded wire
4	+Vs	White

Tolerance unless otherwise noted: ±1

As viewed from connector side

KIRDA0196EB



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Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- Disclaimer
- · Safety consideration
- · Compound opto-semiconductors (photosensors, light emitters)
- Technical note
- · Compound semiconductor photosensors

Information described in this material is current as of November 2022.

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